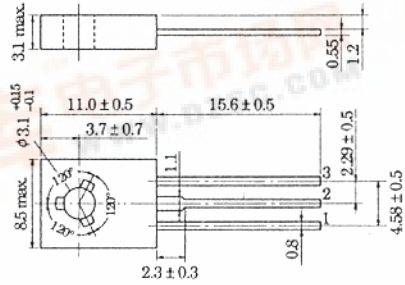
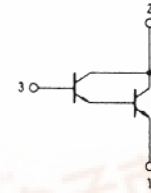


# 2SC2298

SILICON NPN EPITAXIAL  
HIGH GAIN AMPLIFIER



- 1. Emitter
  - 2. Collector
  - 3. Base
- (Dimensions in mm)



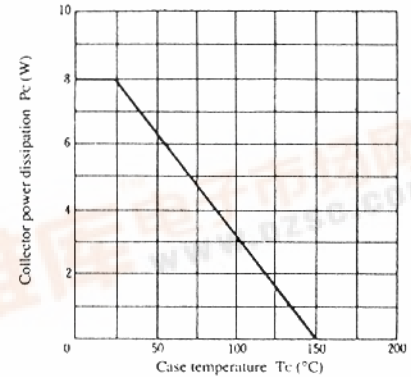
(JEDEC TO-126 MOD.)

## ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Item	Symbol	2SC2298	Unit
Collector to base voltage	V <sub>CB0</sub>	30	V
Collector to emitter voltage	V <sub>CEO</sub>	30	V
Emitter to base voltage	V <sub>EB0</sub>	10	V
Collector current	I <sub>C</sub>	1.0	A
Collector peak current	i <sub>C(peak)</sub>	1.5	A
Collector power dissipation	P <sub>C</sub>	0.8	W
	P <sub>C*</sub>	8	W
Junction temperature	T <sub>J</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

\* Value at T<sub>c</sub> = 25°C

## MAXIMUM COLLECTOR DISSIPATION CURVE



## ELECTRICAL CHARACTERISTICS (Ta=25°C)

Item	Symbol	Test Condition	min.	typ.	max.	Unit
Collector to emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> = 1mA, R <sub>BE</sub> = ∞	30	—	—	V
Emitter cutoff current	I <sub>EBO</sub>	V <sub>EB</sub> = 10V, I <sub>C</sub> = 0	—	—	10	μA
DC current transfer ratio	h <sub>FE1</sub> *	V <sub>CE</sub> = 3V, I <sub>C</sub> = 10mA	4000	—	—	
	h <sub>FE2</sub> *	V <sub>CE</sub> = 3V, I <sub>C</sub> = 100mA	10000	—	—	
	h <sub>FE3</sub> *	V <sub>CE</sub> = 3V, I <sub>C</sub> = 400mA (pulse test)	10000	—	—	
Collector to emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = 400mA, I <sub>B</sub> = 0.1mA (pulse test)	—	—	1.5	V
Base to emitter saturation voltage	V <sub>BE(sat)</sub>		—	—	2.0	V

\* The 2SC2298 is grouped by h<sub>FE</sub> as follows.

